2SC4562

Silicon NPN epitaxial planar type

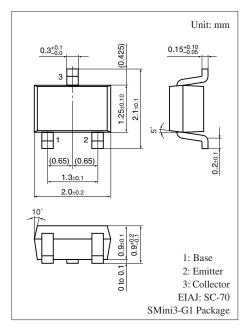
For high-frequency amplification Complementary to 2SA1748

■ Features

- High transition frequency f_T
- \bullet Small collector output capacitance (Common base, input open circuited) C_{ob}
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|------------------|-------------|------|
| Collector-base voltage (Emitter open) | V _{CBO} | 50 | V |
| Collector-emitter voltage (Base open) | V _{CEO} | 50 | V |
| Emitter-base voltage (Collector open) | V _{EBO} | 5 | V |
| Collector current | I_{C} | 50 | mA |
| Collector power dissipation | P _C | 150 | mW |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |



Marking Symbol: AM

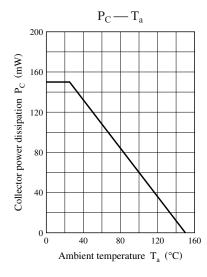
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

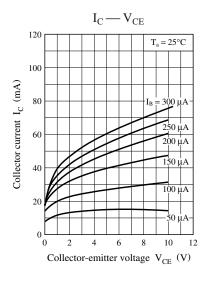
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|---|-----|------|------|------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \ \mu A, I_E = 0$ | 50 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 1 \text{ mA}, I_B = 0$ | 50 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \ \mu A, I_C = 0$ | 5 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 10 \text{ V}, I_{E} = 0$ | | | 0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 10 \text{ V}, I_{B} = 0$ | | | 100 | μΑ |
| Forward current transfer ratio * | h _{FE} | $V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$ | 200 | | 500 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ | | 0.06 | 0.30 | V |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$ | | 250 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ | | 1.5 | | pF |
| (Common base, input open circuited) | | | | | | |

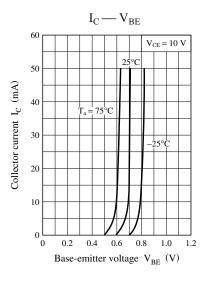
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

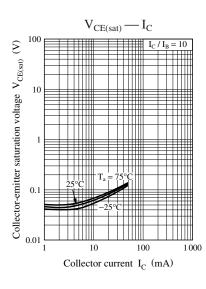
2. *: Rank classification

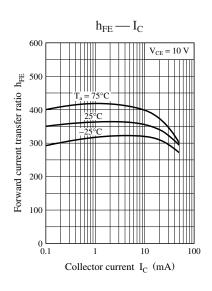
| Rank | Q | R |
|----------|------------|------------|
| h_{FE} | 200 to 400 | 250 to 500 |

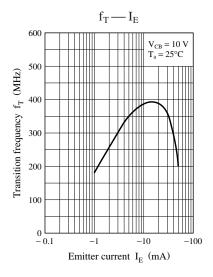


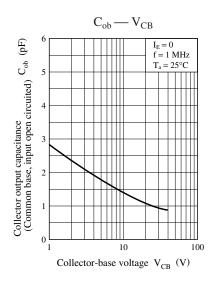












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